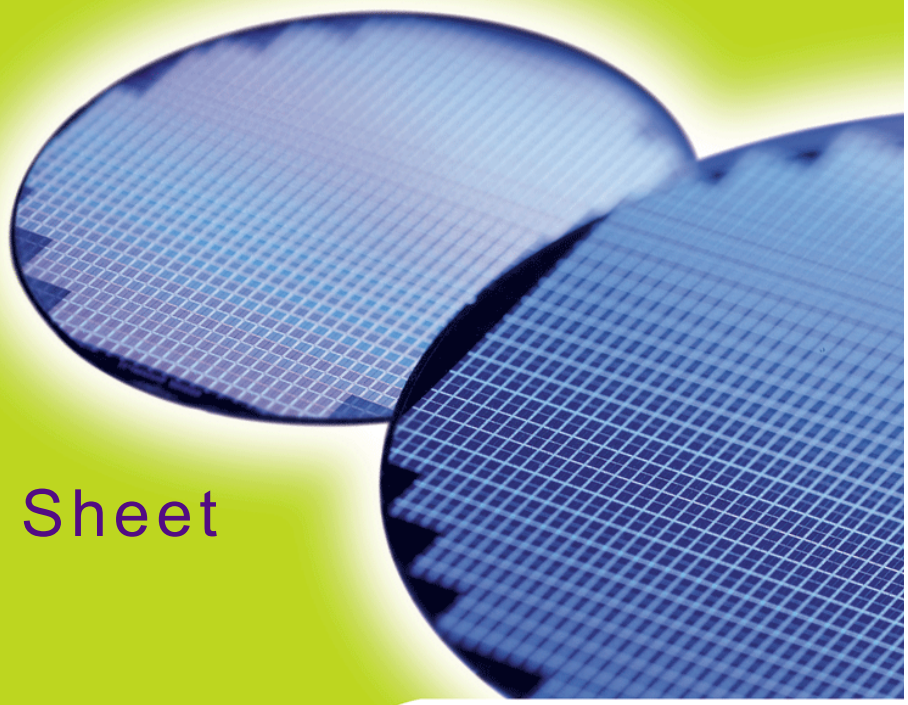
January 2007

HYS64D64020HBDL–5–C
HYS64D64020GBDL–5–C
HYS64D64020HBDL–6–C
HYS64D64020GBDL–6–C

200-Pin Small Outline Dual-In-Line Memory Modules
SO-DIMM
DDR SDRAM



Internet Data Sheet

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HYS64D64020HBDL–5–C, HYS64D64020GBDL–5–C, HYS64D64020HBDL–6–C, HYS64D64020GBDL–6–C Revision History: 2007-01, Rev. 1.21	
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1 Overview

This chapter lists all main features of the product family HYS64D64020[H/G]BDL–[5/6]–C and the ordering information.

1.1 Features

- Non-parity 200-Pin Small Outline Dual-In-Line Memory Modules
- Two ranks 64M × 64 Organization
- JEDEC standard Double Data Rate Synchronous DRAMs (DDR SDRAM)
- Single +2.5 V (± 0.2 V) Power Supply and Single +2.6 V (± 0.1 V) Power Supply for DDR400
- Built with 256 Mbit DDR SDRAMs Organised as × 8 in P–TFBGA–60 Packages
- Programmable CAS Latency, Burst Length, and Wrap Sequence (Sequential & Interleave)
- Auto Refresh (CBR) and Self Refresh
- RAS-lockout Supported $t_{RAP}=t_{RCD}$
- All Inputs and Outputs SSTL_2 Compatible
- Serial Presence Detect with E^2PROM
- Jedec Standard form Factor: 67.60 mm × 31.75 mm × 3.80 mm
- Gold Plated Contacts

TABLE 1
Performance

Part Number Speed Code			–5	–6	Unit
Speed Grade	Component		DDR400B	DDR333B	—
	Module		PC3200–3033	PC2700–2533	—
Max. Clock Frequency	@CL3	f_{CK3}	200	166	MHz
	@CL2.5	$f_{CK2.5}$	166	166	MHz
	@CL2	f_{CK2}	133	133	MHz

1.2 Description

The HYS64D64020HBDL–5–C and HYS64D64020GBDL–5–C are industry standard 200-Pin Small Outline Dual-In-Line Memory Modules (SO-DIMMs) organized as 64M ×64. The memory array is designed with Double Data Rate Synchronous DRAMs (DDR SDRAM). A variety of decoupling capacitors are mounted on the PC board. The DIMMs feature serial presence detect based on a serial E^2PROM device using the 2-pin I^2C protocol. The first 128 bytes are programmed with configuration data and the second 128 bytes are available to the customer.

TABLE 2
Ordering Information

Type	Compliance Code	Description	SDRAM Technology
PC3200 (CL=3.0)			
HYS64D64020GBDL–5–C	PC3200S–3033–1–Z	Two ranks 512 MB SO-DIMM	32 MBit (×8)
PC2700 (CL=2.5)			
HYS64D64020GBDL–6–C	PC2700S–2533–0–Z	Two ranks 512 MB SO-DIMM	32 MBit (×8)

green Product

TABLE 3
Ordering Information for RoHS Compliant Products

Product Type [1)]	Compliance Code	Description	SDRAM Technology
PC3200 (CL=3.0)			
HYS64D64020HBDL–5–C	PC3200S–3033–1–Z	Two ranks 512 MB SO-DIMM	32 MBit (×8)
PC2700 (CL=2.5)			
HYS64D64020HBDL–6–C	PC2700S–2533–0–Z	Two ranks 512 MB SO-DIMM	32 MBit (×8)

1) RoHS Compliant Product: Restriction of the use of certain hazardous substances (RoHS) in electrical and electronic equipment as defined in the directive 2002/95/EC issued by the European Parliament and of the Council of 27 January 2003. These substances include mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls and polybrominated biphenyl ethers.

Notes

1. *All part numbers end with a place code designating the silicon-die revision. Reference information available on request. Example: HYS64D32020GDL-6-B, indicating rev. B dies are used for SDRAM components.*
2. *The Compliance Code is printed on the module labels describing the speed sort (for example “PC2700”), the latencies and SPD code definition (for example “2033–0” means CAS latency of 2.0 clocks, RCD [1)] latency of 3 clocks, Row Precharge latency of 3 clocks, and JEDEC SPD code definiton version 0), and the Raw Card used for this module.*

1) RCD: Row-Column-Delay

2 Pin Configuration

The pin configuration of the Unbuffered Small Outline DDR SDRAM DIMM is listed by function in **Table 4** (184 pins). The abbreviations used in columns Pin and Buffer Type are explained in **Table 5** and **Table 6** respectively. The pin numbering is depicted in **Figure 1**.

TABLE 4
Pin Configuration of SO-DIMM

Pin#	Name	Pin Type	Buffer Type	Function
Clock Signals				
35	CK0	I	SSTL	**Clock Signal**
160	CK1	I	SSTL	**Clock Signal**
89	CK2	I	SSTL	**Clock Signal** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC type module*
37	$\overline{CK0}$	I	SSTL	**Complement Clock**
158	$\overline{CK1}$	I	SSTL	**Complement Clock**
91	$\overline{CK2}$	I	SSTL	**Complement Clock** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC type module*
96	CKE0	I	SSTL	**Clock Enable Rank 0**
95	CKE1	I	SSTL	**Clock Enable Rank 1** *Note: 2-rank module*
	NC	NC	—	*Note: 1-rank module*
Control Signals				
121	$\overline{S0}$	I	SSTL	**Chip Select Rank 0**
122	$\overline{S1}$	I	SSTL	**Chip Select Rank 1** *Note: 2-ranks module*
	NC	NC	—	*Note: 1-rank module*
118	$\overline{RAS}$	I	SSTL	**Row Address Strobe**
120	$\overline{CAS}$	I	SSTL	**Column Address Strobe**
119	$\overline{WE}$	I	SSTL	**Write Enable**
Address Signals				
117	BA0	I	SSTL	**Bank Address Bus 1:0**
116	BA1	I	SSTL	

Pin#	Name	Pin Type	Buffer Type	Function
112	A0	I	SSTL	**Address Bus 11:0**
111	A1	I	SSTL	
110	A2	I	SSTL	
109	A3	I	SSTL	
108	A4	I	SSTL	
107	A5	I	SSTL	
106	A6	I	SSTL	
105	A7	I	SSTL	
102	A8	I	SSTL	
101	A9	I	SSTL	
115	A10	I	SSTL	
	AP	I	SSTL	
100	A11	I	SSTL	
99	A12	I	SSTL	**Address Signal 12** *Note: Module based on 256 Mbit or larger dies*
	NC	NC	—	*Note: 128 Mbit based module*
123	A13	I	SSTL	**Address Signal 13** *Note: 1 Gbit based module*
	NC	NC	—	*Note: Module based on 512 Mbit or smaller dies*
Data Signals				
5	DQ0	I/O	SSTL	**Data Bus 63:0**
7	DQ1	I/O	SSTL	
13	DQ2	I/O	SSTL	
17	DQ3	I/O	SSTL	
6	DQ4	I/O	SSTL	
8	DQ5	I/O	SSTL	
14	DQ6	I/O	SSTL	
18	DQ7	I/O	SSTL	
19	DQ8	I/O	SSTL	
23	DQ9	I/O	SSTL	
29	DQ10	I/O	SSTL	
31	DQ11	I/O	SSTL	
20	DQ12	I/O	SSTL	
24	DQ13	I/O	SSTL	

Pin#	Name	Pin Type	Buffer Type	Function
30	DQ14	I/O	SSTL	**Data Bus 63:0**
32	DQ15	I/O	SSTL	
41	DQ16	I/O	SSTL	
43	DQ17	I/O	SSTL	
49	DQ18	I/O	SSTL	
53	DQ19	I/O	SSTL	
42	DQ20	I/O	SSTL	
44	DQ21	I/O	SSTL	
50	DQ22	I/O	SSTL	
54	DQ23	I/O	SSTL	
55	DQ24	I/O	SSTL	
59	DQ25	I/O	SSTL	
65	DQ26	I/O	SSTL	
67	DQ27	I/O	SSTL	
56	DQ28	I/O	SSTL	
60	DQ29	I/O	SSTL	
66	DQ30	I/O	SSTL	
68	DQ31	I/O	SSTL	
127	DQ32	I/O	SSTL	
129	DQ33	I/O	SSTL	
135	DQ34	I/O	SSTL	
139	DQ35	I/O	SSTL	
128	DQ36	I/O	SSTL	
130	DQ37	I/O	SSTL	
136	DQ38	I/O	SSTL	
140	DQ39	I/O	SSTL	
141	DQ40	I/O	SSTL	
145	DQ41	I/O	SSTL	
151	DQ42	I/O	SSTL	
153	DQ43	I/O	SSTL	
142	DQ44	I/O	SSTL	
146	DQ45	I/O	SSTL	
152	DQ46	I/O	SSTL	
154	DQ47	I/O	SSTL	
163	DQ48	I/O	SSTL	
165	DQ49	I/O	SSTL	
171	DQ50	I/O	SSTL	
175	DQ51	I/O	SSTL	
164	DQ52	I/O	SSTL	
166	DQ53	I/O	SSTL	

Pin#	Name	Pin Type	Buffer Type	Function
172	DQ54	I/O	SSTL	**Data Bus 63:0**
176	DQ55	I/O	SSTL	
177	DQ56	I/O	SSTL	
181	DQ57	I/O	SSTL	
187	DQ58	I/O	SSTL	
189	DQ59	I/O	SSTL	
178	DQ60	I/O	SSTL	
182	DQ61	I/O	SSTL	
188	DQ62	I/O	SSTL	
190	DQ63	I/O	SSTL	
71	CB0	I/O	SSTL	**Check Bit 0** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
73	CB1	I/O	SSTL	**Check Bit 1** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
79	CB2	I/O	SSTL	**Check Bit 2** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
83	CB3	I/O	SSTL	**Check Bit 3** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
72	CB4	I/O	SSTL	**Check Bit 4** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
74	CB5	I/O	SSTL	**Check Bit 5** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
80	CB6	I/O	SSTL	**Check Bit 6** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
84	CB7	I/O	SSTL	**Check Bit 7** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*

Pin#	Name	Pin Type	Buffer Type	Function
11	DQS0	I/O	SSTL	**Data Strobes 7:0**
25	DQS1	I/O	SSTL	
47	DQS2	I/O	SSTL	
61	DQS3	I/O	SSTL	
133	DQS4	I/O	SSTL	
147	DQS5	I/O	SSTL	
169	DQS6	I/O	SSTL	
183	DQS7	I/O	SSTL	
77	DQS8	I/O	SSTL	**Data Strobe 8** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
12	DM0	I	SSTL	**Data Mask 7:0**
26	DM1	I	SSTL	
48	DM2	I	SSTL	
62	DM3	I	SSTL	
134	DM4	I	SSTL	
148	DM5	I	SSTL	
170	DM6	I	SSTL	
184	DM7	I	SSTL	
78	DM8	I	SSTL	**Data Mask 8** *Note: ECC type module*
	NC	NC	—	*Note: Non-ECC module*
EEPROM				
195	SCL	I	CMOS	**Serial Bus Clock**
193	SDA	I/O	OD	**Serial Bus Data**
194	SA0	I	CMOS	**Slave Address Select Bus 2:0**
196	SA1	I	CMOS	
198	SA2	I	CMOS	
Power Supplies				
1,2	V_{REF}	AI	—	**I/O Reference Voltage**
197	V_{DDSPD}	PWR	—	**EEPROM Power Supply**

Pin#	Name	Pin Type	Buffer Type	Function
9,10,21, 22, 33, 34, 36, 45, 46, 57, 58, 69, 70, 81, 82, 92, 93, 94, 113, 114, 131, 132, 143, 144, 155, 156, 157, 167, 168, 179, 180, 191, 192	V_{DD}	PWR	—	**Power Supply**

Pin#	Name	Pin Type	Buffer Type	Function
3,4, 15, 16, 27, 28, 38, 39, 40, 51, 52, 63, 64, 75, 76, 87, 88, 90, 103, 104, 125, 126, 137, 138, 149, 150, 159, 161, 162, 173, 174, 185, 186	V_{SS}	GND	—	**Ground Plane**
Other Pins				
199	V_{DDID}	O	OD	V_{DD} **Identification**
85, 86, 97, 98, 124, 200	NC	NC	—	**Not connected**

TABLE 5
Abbreviations for Pin Type

Abbreviation	Description
I	Standard input-only pin. Digital levels.
O	Output. Digital levels.
I/O	I/O is a bidirectional input/output signal.
AI	Input. Analog levels.
PWR	Power
GND	Ground
NC	Not Connected

TABLE 6
Abbreviations for Buffer Type

Abbreviation	Description
SSTL	Serial Stub Terminalted Logic (SSTL2)
LV-CMOS	Low Voltage CMOS
CMOS	CMOS Levels
OD	Open Drain. The corresponding pin has 2 operational states, active low and tristate, and allows multiple devices to share as a wire-OR.

FIGURE 1
Pin Configuration Diagram 200-Pin SO-DIMM

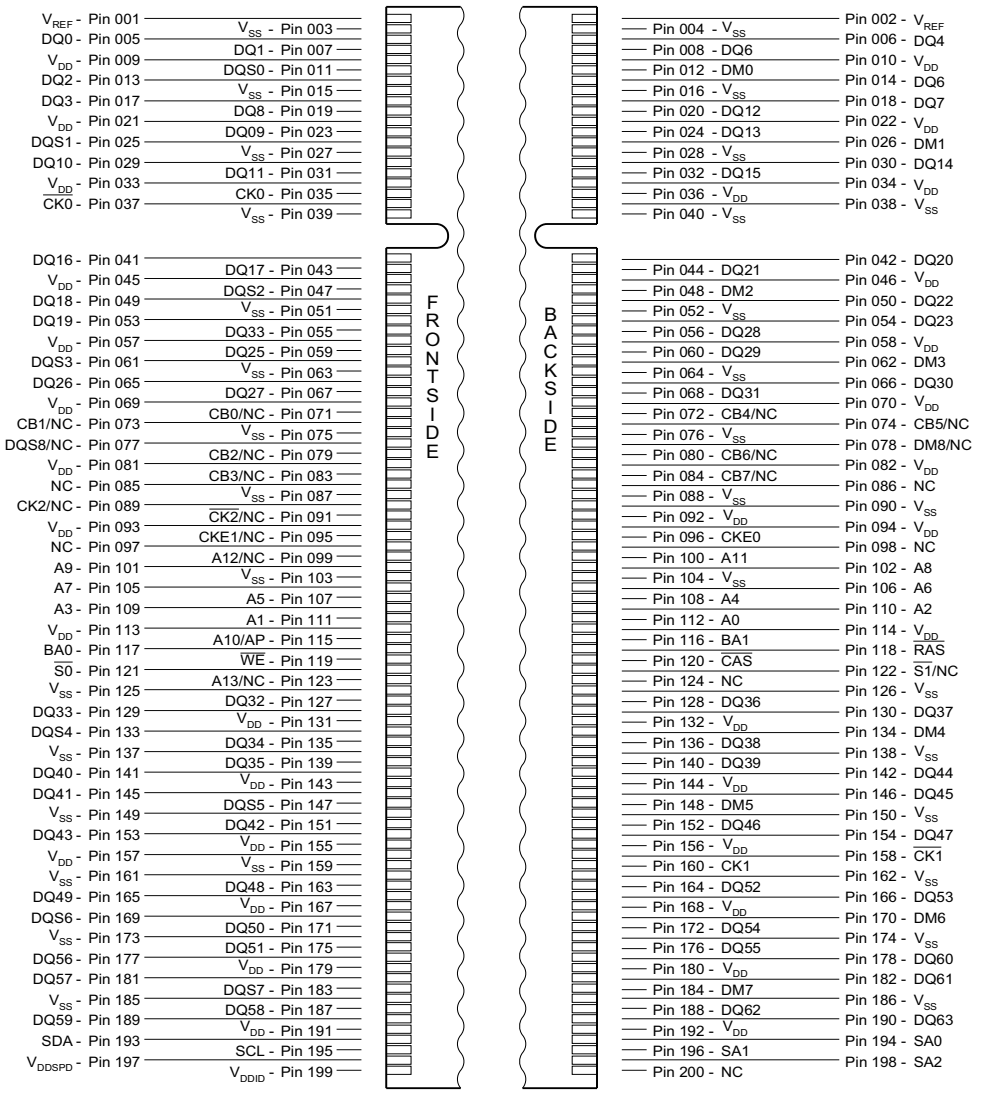

TABLE 7
Address Format

Density	Organization	Memory Ranks	SDRAMs	# of SDRAMs	# of row/bank/ columns bits	Refresh	Period	Interval
512MB	64M ×64	2	32M ×8	16	13/2/10	8K	64 ms	7.8 ms

3 Electrical Characteristics

This chapter lists the electrical characteristics.

3.1 Operating Conditions

This chapter contains the operating conditions tables.

TABLE 8
Absolute Maximum Ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Voltage on I/O pins relative to V_{SS}	V_{IN}, V_{OUT}	–0.5	—	V_{DDQ} + 0.5	V	—
Voltage on inputs relative to V_{SS}	V_{IN}	–1	—	+3.6	V	—
Voltage on V_{DD} supply relative to V_{SS}	V_{DD}	–1	—	+3.6	V	—
Voltage on V_{DDQ} supply relative to V_{SS}	V_{DDQ}	–1	—	+3.6	V	—
Operating temperature (ambient)	T_A	0	—	+70	°C	—
Storage temperature (plastic)	T_{STG}	-55	—	+150	°C	—
Power dissipation (per SDRAM component)	PD	—	1	—	W	—
Short circuit output current	I_{OUT}	—	50	—	mA	—

Attention: Permanent damage to the device may occur if "Absolute Maximum Ratings" are exceeded. This is a stress rating only, and functional operation should be restricted to recommended operation conditions. Exposure to absolute maximum rating conditions for extended periods of time may affect device reliability and exceeding only one of the values may cause irreversible damage to the integrated circuit.

TABLE 9
Electrical Characteristics and DC Operating Conditions

Parameter	Symbol	Values			Unit	Note[1] / Test Condition
		Min.	Typ.	Max.		
Device Supply Voltage	V_{DD}	2.3	2.5	2.7	V	$f_{CK} \leq$ 166 MHz
Device Supply Voltage	V_{DD}	2.5	2.6	2.7	V	f_{CK} > 166 MHz [2]
Output Supply Voltage	V_{DDQ}	2.3	2.5	2.7	V	$f_{CK} \leq$ 166 MHz [3]
Output Supply Voltage	V_{DDQ}	2.5	2.6	2.7	V	f_{CK} > 166 MHz [2)3)]
EEPROM supply voltage	V_{DDSPD}	2.3	2.5	3.6	V	—
Supply Voltage, I/O Supply Voltage	V_{SS}, V_{SSQ}	0	—	0	V	—
Input Reference Voltage	V_{REF}	0.49 × V_{DDQ}	0.5 × V_{DDQ}	0.51 × V_{DDQ}	V	[4]
I/O Termination Voltage (System)	V_{TT}	V_{REF} – 0.04	—	V_{REF} + 0.04	V	[5]
Input High (Logic1) Voltage	$V_{IH(DC)}$	V_{REF} + 0.15	—	V_{DDQ} + 0.3	V	[6]
Input Low (Logic0) Voltage	$V_{IL(DC)}$	–0.3	—	V_{REF} – 0.15	V	[5]
Input Voltage Level, CK and $\overline{CK}$ Inputs	$V_{IN(DC)}$	–0.3	—	V_{DDQ} + 0.3	V	[5]
Input Differential Voltage, CK and $\overline{CK}$ Inputs	$V_{ID(DC)}$	0.36	—	V_{DDQ} + 0.6	V	[5)7)]
VI-Matching Pull-up Current to Pull-down Current	VI_{Ratio}	0.71	—	1.4	—	[8]
Input Leakage Current	I_I	–2	—	2	µA	Any input 0 V $\leq V_{IN} \leq V_{DD}$; All other pins not under test = 0 V [9]
Output Leakage Current	I_{OZ}	–5	—	5	µA	DQs are disabled; 0 V $\leq V_{OUT} \leq V_{DDQ}$ [9]
Output High Current, Normal Strength Driver	I_{OH}	—	—	–16.2	mA	V_{OUT} = 1.95 V
Output Low Current, Normal Strength Driver	I_{OL}	16.2	—	—	mA	V_{OUT} = 0.35 V

1) 0 °C ≤ T_A ≤ 70 °C; V_{DDQ} = 2.5 V ± 0.2 V, V_{DD} = +2.5 V ± 0.2 V; V_{DDQ} = 2.6 V ± 0.1 V, V_{DD} = +2.6 V ± 0.1 V (DDR400);
2) DDR400 conditions apply for all clock frequencies above 166 MHz
3) Under all conditions, V_{DDQ} must be less than or equal to V_{DD}.
4) Peak to peak AC noise on V_{REF} may not exceed ± 2% VREF (DC). VREF is also expected to track noise variations in V_{DDQ}.
5) V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF}, and must track variations in the DC level of V_{REF}.
6) Inputs are not recognized as valid until V_{REF} stabilizes.
7) V_{ID} is the magnitude of the difference between the input level on CK and the input level on $\overline{CK}$.
8) The ratio of the pull-up current to the pull-down current is specified for the same temperature and voltage, over the entire temperature and voltage range, for device drain to source voltage from 0.25 to 1.0 V. For a given output, it represents the maximum difference between pull-up and pull-down drivers due to process variation.
9) Values are shown per pin.

3.2 Current Specification and Conditions

TABLE 10
I_{DD} Conditions

Parameter	Symbol
Operating Current 0 One bank; active/ precharge; DQ, DM, and DQS inputs changing once per clock cycle; Address and control inputs changing once every two clock cycles.	I_{DD0}
Operating Current 1 One bank; active/read/precharge; Burst Length = 4; see component data sheet.	I_{DD1}
Precharge Power-Down Standby Current All banks idle; power-down mode; CKE ≤ $V_{IL,MAX}$	I_{DD2P}
Precharge Floating Standby Current $\overline{CS}$ ≥ $V_{IH,,MIN}$, all banks idle; CKE ≥ $V_{IH,MIN}$; Address and other control inputs changing once per clock cycle; V_{IN} = V_{REF} for DQ, DQS and DM.	I_{DD2F}
Precharge Quiet Standby Current $\overline{CS}$ ≥ V_{IHMIN}, all banks idle; CKE ≥ $V_{IH,MIN}$; V_{IN} = V_{REF} for DQ, DQS and DM; Address and other control inputs stable at ≥ $V_{IH,MIN}$ or ≤ $V_{IL,MAX}$.	I_{DD2Q}
Active Power-Down Standby Current One bank active; power-down mode; CKE ≤ V_{ILMAX}; V_{IN} = V_{REF} for DQ, DQS and DM.	I_{DD3P}
Active Standby Current One bank active; $\overline{CS}$ ≥ $V_{IH,MIN}$; CKE ≥ $V_{IH,MIN}$; t_{RC} = $t_{RAS,MAX}$; DQ, DM and DQS inputs changing twice per clock cycle; Address and control inputs changing once per clock cycle.	I_{DD3N}
Operating Current Read One bank active; Burst Length = 2; reads; continuous burst; Address and control inputs changing once per clock cycle; 50% of data outputs changing on every clock edge; CL = 2 for DDR266(A), CL = 3 for DDR333 and DDR400B; I_{OUT} = 0 mA	I_{DD4R}
Operating Current Write One bank active; Burst Length = 2; writes; continuous burst; Address and control inputs changing once per clock cycle; 50% of data outputs changing on every clock edge; CL = 2 for DDR266(A), CL = 3 for DDR333 and DDR400B	I_{DD4W}
Auto-Refresh Current t_{RC} = t_{RFCMIN}, burst refresh	I_{DD5}
Self-Refresh Current CKE ≤ 0.2 V; external clock on	I_{DD6}
Operating Current 7 Four bank interleaving with Burst Length = 4; see component data sheet.	I_{DD7}

TABLE 11

I_{DD} Specification for HYS64D64020[G/H]BDL–5–C

Product Type	HYS64D64020GBDL–5–C HYS64D64020HBDL–5–C		Unit	Note[1)2)]
Organization	512MB			
	× 64			
	2 Ranks			
	–5			
Symbol	Typ.	Max.		
I_{DD0}	940	1150	mA	3)
I_{DD1}	1100	1310	mA	4)
I_{DD2P}	480	580	mA	5)
I_{DD2F}	320	450	mA	5)
I_{DD2Q}	210	290	mA	5)
I_{DD3P}	610	720	mA	5)
I_{DD3N}	690	860	mA	5)
I_{DD4R}	1140	1390	mA	3)4)
I_{DD4W}	1140	1470	mA	3)
I_{DD5}	360	450	mA	3)
I_{DD6}	16	17.6	mA	5)
I_{DD7}	2020	2430	mA	3)4)

1) Module I_{DD} values are calculated on the basis of component I_{DD} and can be measured differently according to DQ loading capacity.
2) Test condition for maximum values: V_{DD} = 2.7 V, T_A = 10 °C
3) The module I_{DDx} values are calculated from the I_{DDx} values of the component data sheet as follows: **m** × I_{DDx} [component] + **n** × I_{DD3N} [component] with **m** and **n** number of components of rank 1 and 2; **n**=0 for 1 rank modules
4) DQ I/O (I_{DDQ}) currents are not included in the calculations (see note [1)])
5) The module I_{DDx} values are calculated from the corrponent I_{DDx} data sheet values as: (**m** + **n**) × I_{DDx} [component]

TABLE 12

I_{DD} Specification for HYS64D64020[G/H]BDL–6–C

Product Type	HYS64D64020GBDL–6—C HYS64D64020HBDL–6–C		Unit	Note[1)2)]
Organization	512MB			
	× 64			
	2 Ranks			
	–6			
Symbol	Typ.	Max.		
I_{DD0}	810	960	mA	3)
I_{DD1}	930	1120	mA	3)4)
I_{DD2P}	400	480	mA	5)
I_{DD2F}	270	380	mA	5)
I_{DD2Q}	180	240	mA	5)
I_{DD3P}	510	610	mA	5)
I_{DD3N}	580	720	mA	5)
I_{DD4R}	970	1160	mA	3)4)
I_{DD4W}	1010	1240	mA	3)
I_{DD5}	300	380	mA	3)
I_{DD6}	16	17.6	mA	5)
I_{DD7}	1730	2080	mA	3)4)

1) Module I_{DD} values are calculated on the basis of component I_{DD} and can be measured differently according to DQ loading capacity.
2) Test condition for maximum values: V_{DD} = 2.7 V, T_A = 10 °C
3) The module I_{DDx} values are calculated from the I_{DDx} values of the component data sheet as follows: **m** × I_{DDx} [component] + **n** × I_{DD3N} [component] with **m** and **n** number of components of rank 1 and 2; **n**=0 for 1 rank modules
4) DQ I/O (I_{DDQ}) currents are not included in the calculations (see note 1)
5) The module I_{DDx} values are calculated from the corrponent I_{DDx} data sheet values as: (**m** + **n**) × I_{DDx} [component]

TABLE 13
AC Timing - Absolute Specifications for PC3200 and PC2700

Parameter	Symbol	–5		–6		Unit	Note[1] / Test Condition
		DDR400B		DDR333			
		Min.	Max.	Min.	Max.		
DQ output access time from CK/$\overline{CK}$	t_{AC}	–0.5	+0.5	–0.7	+0.7	ns	2)3)4)5)
CK high-level width	t_{CH}	0.45	0.55	0.45	0.55	t_{CK}	2)3)4)5)
Clock cycle time	t_{CK}	5	8	6	12	ns	CL = 3.0 2)3)4)5)
		6	12	6	12	ns	CL = 2.5 2)3)4)5)
		7.5	12	7.5	12	ns	CL = 2.0 2)3)4)5)
CK low-level width	t_{CL}	0.45	0.55	0.45	0.55	t_{CK}	2)3)4)5)
Auto precharge write recovery + precharge time	t_{DAL}	$(t_{WR}/t_{CK})+(t_{RP}/t_{CK})$				t_{CK}	2)3)4)5)6)
DQ and DM input hold time	t_{DH}	0.4	—	0.45	—	ns	2)3)4)5)
DQ and DM input pulse width (each input)	t_{DIPW}	1.75	—	1.75	—	ns	2)3)4)5)6)
DQS output access time from CK/$\overline{CK}$	t_{DQSCK}	–0.6	+0.6	–0.6	+0.6	ns	2)3)4)5)
DQS input low (high) pulse width (write cycle)	$t_{DQSL,H}$	0.35	—	0.35	—	t_{CK}	2)3)4)5)
DQS-DQ skew (DQS and associated DQ signals)	t_{DQSQ}	—	+0.40	—	+0.40	ns	TFBGA 2)3)4)5)
Write command to 1st DQS latching transition	t_{DQSS}	0.72	1.25	0.75	1.25	t_{CK}	2)3)4)5)
DQ and DM input setup time	t_{DS}	0.4	—	0.45	—	ns	2)3)4)5)
DQS falling edge hold time from CK (write cycle)	t_{DSH}	0.2	—	0.2	—	t_{CK}	2)3)4)5)
DQS falling edge to CK setup time (write cycle)	t_{DSS}	0.2	—	0.2	—	t_{CK}	2)3)4)5)
Clock Half Period	t_{HP}	Min. (t_{CL}, t_{CH})		Min. (t_{CL}, t_{CH})		ns	2)3)4)5)
Data-out high-impedance time from CK/$\overline{CK}$	t_{HZ}	—	+0.7	–0.7	+0.7	ns	2)3)4)5)7)
Address and control input hold time	t_{IH}	0.6	—	0.75	—	ns	Fast slew rate 3)4)5)6)8)
		0.7	—	0.8	—	ns	Slow slew rate 3)4)5)6)8)
Control and Addr. input pulse width (each input)	t_{IPW}	2.2	—	2.2	—	ns	2)3)4)5)9)

Parameter	Symbol	–5		–6		Unit	Note[1] / Test Condition
		DDR400B		DDR333			
		Min.	Max.	Min.	Max.		
Address and control input setup time	t_{IS}	0.6	—	0.75	—	ns	Fast slew rate[3)4)5)6)8)]
		0.7	—	0.8	—	ns	Slow slew rate[3)4)5)6)8)]
Data-out low-impedance time from CK/$\overline{CK}$	t_{LZ}	–0.7	+0.7	–0.7	+0.7	ns	2)3)4)5)7)
Mode register set command cycle time	t_{MRD}	2	—	2	—	t_{CK}	2)3)4)5)
DQ/DQS output hold time	t_{QH}	$t_{HP} - t_{QHS}$		$t_{HP} - t_{QHS}$		ns	2)3)4)5)
Data hold skew factor	t_{QHS}	—	+0.50	—	+0.50	ns	TFBGA[2)3)4)5)]
Active to Autoprecharge delay	t_{RAP}	t_{RCD}	—	t_{RCD}	—	ns	2)3)4)5)
Active to Precharge command	t_{RAS}	40	70E+3	42	70E+3	ns	2)3)4)5)
Active to Active/Auto-refresh command period	t_{RC}	55	—	60	—	ns	2)3)4)5)
Active to Read or Write delay	t_{RCD}	15	—	18	—	ns	2)3)4)5)
Average Periodic Refresh Interval	t_{REFI}	—	7.8	—	7.8	µs	2)3)4)5)10)
Auto-refresh to Active/Auto-refresh command period	t_{RFC}	65	—	72	—	ns	2)3)4)5)
Precharge command period	t_{RP}	15	—	18	—	ns	2)3)4)5)
Read preamble	t_{RPRE}	0.9	1.1	0.9	1.1	t_{CK}	2)3)4)5)
Read postamble	t_{RPST}	0.40	0.60	0.40	0.60	t_{CK}	2)3)4)5)
Active bank A to Active bank B command	t_{RRD}	10	—	12	—	ns	2)3)4)5)
Write preamble	t_{WPRE}	0.25	—	0.25	—	t_{CK}	2)3)4)5)
Write preamble setup time	t_{WPRES}	0	—	0	—	ns	2)3)4)5)11)
Write postamble	t_{WPST}	0.40	0.60	0.40	0.60	t_{CK}	2)3)4)5)12)
Write recovery time	t_{WR}	15	—	15	—	ns	2)3)4)5)
Internal write to read command delay	t_{WTR}	2	—	1	—	t_{CK}	2)3)4)5)
Exit self-refresh to non-read command	t_{XSNR}	75	—	75	—	ns	2)3)4)5)
Exit self-refresh to read command	t_{XSRD}	200	—	200	—	t_{CK}	2)3)4)5)

1) 0 °C ≤ T_A ≤ 70 °C; V_{DDQ} = 2.5 V ± 0.2 V, V_{DD} = +2.5 V ± 0.2 V (DDR333); V_{DDQ} = 2.6 V ± 0.1 V, V_{DD} = +2.6 V ± 0.1 V (DDR400)
2) Input slew rate ≥ 1 V/ns for DDR400, DDR333
3) The CK/$\overline{CK}$ input reference level (for timing reference to CK/$\overline{CK}$) is the point at which CK and $\overline{CK}$ cross: the input reference level for signals other than CK/$\overline{CK}$, is V_{REF}. CK/$\overline{CK}$ slew rate are ≥ 1.0 V/ns.
4) Inputs are not recognized as valid until V_{REF} stabilizes.
5) The Output timing reference level, as measured at the timing reference point indicated in AC Characteristics (note 3) is V_{TT}.
6) For each of the terms, if not already an integer, round to the next highest integer. t_{CK} is equal to the actual system clock cycle time.
7) t_{HZ} and t_{LZ} transitions occur in the same access time windows as valid data transitions. These parameters are not referred to a specific voltage level, but specify when the device is no longer driving (HZ), or begins driving (LZ).
8) Fast slew rate ≥ 1.0 V/ns , slow slew rate ≥ 0.5 V/ns and < 1 V/ns for command/address and CK & $\overline{CK}$ slew rate > 1.0 V/ns, measured between $V_{IH(ac)}$ and $V_{IL(ac)}$.

9) These parameters guarantee device timing, but they are not necessarily tested on each device.
10) A maximum of eight Autorefresh commands can be posted to any given DDR SDRAM device.
11) The specific requirement is that DQS be valid (HIGH,LOW, or some point on a valid transition) on or before this CK edge. A valid transition is defined as monotonic and meeting the input slew rate specificationsof the device. When no writes were previously in progress on the bus, DQS will be transitioning from Hi-Z to logic LOW. If a previous write was in progress, DQS could be HIGH, LOW at this time, depending on t_{DQSS}.
12) The maximum limit for this parameter is not a device limit. The device operates with a greater value for this parameter, but system performance (bus turnaround) degrades accordingly.

4 SPD Codes

This chapter lists all hexadecimal byte values stored in the EEPROM of the products described in this data sheet. SPD stands for serial presence detect. All values with XX in the table are module specific bytes which are defined during production.

List of SPD Code Tables

TABLE 14
SPD Codes for HYS64D64020HBDL–5–C and HYS64D64020GBDL–5–C

Product Type		HYS64D64020GBDL–5–C	HYS64D64020HBDL–5–C
Organization		512MB	512MB
		×64	×64
		2 Ranks (×8)	2 Ranks (×8)
Label Code		PC3200S–30331	PC3200S–30331
JEDEC SPD Revision		Rev. 1.0	Rev. 1.0
Byte#	**Description**	**HEX**	**HEX**
0	Programmed SPD Bytes in E^2PROM	80	80
1	Total number of Bytes in E^2PROM	08	08
2	Memory Type (DDR = 07h)	07	07
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	Number of DIMM Ranks	02	02
6	Data Width (LSB)	40	40
7	Data Width (MSB)	00	00
8	Interface Voltage Levels	04	04
9	t_{CK} @ CL_{max} (Byte 18) [ns]	50	50
10	t_{AC} SDRAM @ CL_{max} (Byte 18) [ns]	50	50
11	Error Correction Support	00	00
12	Refresh Rate	82	82
13	Primary SDRAM Width	08	08
14	Error Checking SDRAM Width	00	00
15	t_{CCD} [cycles]	01	01
16	Burst Length Supported	0E	0E
17	Number of Banks on SDRAM Device	04	04
18	CAS Latency	1C	1C
19	CS Latency	01	01
20	Write Latency	02	02

Product Type		HYS64D64020GBDL–5–C	HYS64D64020HBDL–5–C
Organization		512MB	512MB
		×64	×64
		2 Ranks (×8)	2 Ranks (×8)
Label Code		PC3200S–30331	PC3200S–30331
JEDEC SPD Revision		Rev. 1.0	Rev. 1.0
Byte#	**Description**	**HEX**	**HEX**
21	DIMM Attributes	20	20
22	Component Attributes	C1	C1
23	t_{CK} @ CL_{max} -0.5 (Byte 18) [ns]	60	60
24	t_{AC} SDRAM @ CL_{max}-0.5 [ns]	50	50
25	t_{CK} @ CL_{max} -1 (Byte 18) [ns]	75	75
26	t_{AC} SDRAM @ CL_{max} -1 [ns]	50	50
27	t_{RPmin} [ns]	3C	3C
28	t_{RRDmin} [ns]	28	28
29	t_{RCDmin} [ns]	3C	3C
30	t_{RASmin} [ns]	28	28
31	Module Density per Rank	40	40
32	t_{AS}, t_{CS} [ns]	60	60
33	t_{AH}, t_{CH} [ns]	60	60
34	t_{DS} [ns]	40	40
35	t_{DH} [ns]	40	40
36 - 40	Not used	00	00
41	t_{RCmin} [ns]	37	37
42	t_{RFCmin} [ns]	41	41
43	t_{CKmax} [ns]	28	28
44	$t_{DQSQmax}$ [ns]	28	28
45	t_{QHSmax} [ns]	50	50
46	Not used	00	00
47	DIMM PCB Height	01	01
48 - 61	Not used	00	00
62	SPD Revision	10	10
63	Checksum of Byte 0-62	0F	0F
64	Manufacturer’s JEDEC ID Code (1)	7F	7F
65	Manufacturer’s JEDEC ID Code (2)	7F	7F
66	Manufacturer’s JEDEC ID Code (3)	7F	7F
67	Manufacturer’s JEDEC ID Code (4)	7F	7F
68	Manufacturer’s JEDEC ID Code (5)	7F	7F
69	Manufacturer’s JEDEC ID Code (6)	51	51
70	Manufacturer’s JEDEC ID Code (7)	00	00

Product Type		**HYS64D64020GBDL–5–C**	**HYS64D64020HBDL–5–C**
Organization		**512MB**	**512MB**
		×64	**×64**
		2 Ranks (×8)	**2 Ranks (×8)**
Label Code		**PC3200S–30331**	**PC3200S–30331**
JEDEC SPD Revision		**Rev. 1.0**	**Rev. 1.0**
Byte#	**Description**	**HEX**	**HEX**
71	Manufacturer's JEDEC ID Code (8)	00	00
72	Module Manufacturer Location	xx	xx
73	Part Number, Char 1	36	36
74	Part Number, Char 2	34	34
75	Part Number, Char 3	44	44
76	Part Number, Char 4	36	36
77	Part Number, Char 5	34	34
78	Part Number, Char 6	30	30
79	Part Number, Char 7	32	32
80	Part Number, Char 8	30	30
81	Part Number, Char 9	47	48
82	Part Number, Char 10	42	42
83	Part Number, Char 11	44	44
84	Part Number, Char 12	4C	4C
85	Part Number, Char 13	35	35
86	Part Number, Char 14	43	43
87	Part Number, Char 15	20	20
88	Part Number, Char 16	20	20
89	Part Number, Char 17	20	20
90	Part Number, Char 18	20	20
91	Module Revision Code	1x	1x
92	Test Program Revision Code	xx	xx
93	Module Manufacturing Date Year	xx	xx
94	Module Manufacturing Date Week	xx	xx
95 - 98	Module Serial Number	xx	xx
99 - 127	Not used	00	00

TABLE 15
SPD Codes for HYS64D64020HBDL–6–C and HYS64D64020GBDL–6–C

Product Type		HYS64D64020GBDL–6–C	HYS64D64020HBDL–6–C
Organization		512MB	512MB
		×64	×64
		2 Ranks (×8)	2 Ranks (×8)
Label Code		PC2700S–25330	PC2700S–25330
JEDEC SPD Revision		Rev. 0.0	Rev. 0.0
Byte#	**Description**	**HEX**	**HEX**
0	Programmed SPD Bytes in E^2PROM	80	80
1	Total number of Bytes in E^2PROM	08	08
2	Memory Type (DDR = 07h)	07	07
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	Number of DIMM Ranks	02	02
6	Data Width (LSB)	40	40
7	Data Width (MSB)	00	00
8	Interface Voltage Levels	04	04
9	t_{CK} @ CL_{max} (Byte 18) [ns]	60	60
10	t_{AC} SDRAM @ CL_{max} (Byte 18) [ns]	70	70
11	Error Correction Support	00	00
12	Refresh Rate	82	82
13	Primary SDRAM Width	08	08
14	Error Checking SDRAM Width	00	00
15	t_{CCD} [cycles]	01	01
16	Burst Length Supported	0E	0E
17	Number of Banks on SDRAM Device	04	04
18	CAS Latency	0C	0C
19	CS Latency	01	01
20	Write Latency	02	02
21	DIMM Attributes	20	20
22	Component Attributes	C1	C1
23	t_{CK} @ CL_{max} -0.5 (Byte 18) [ns]	75	75
24	t_{AC} SDRAM @ CL_{max} -0.5 [ns]	70	70
25	t_{CK} @ CL_{max} -1 (Byte 18) [ns]	00	00
26	t_{AC} SDRAM @ CL_{max} -1 [ns]	00	00
27	t_{RPmin} [ns]	48	48
28	t_{RRDmin} [ns]	30	30
29	t_{RCDmin} [ns]	48	48

Product Type		HYS64D64020GBDL–6–C	HYS64D64020HBDL–6–C
Organization		512MB	512MB
		×64	×64
		2 Ranks (×8)	2 Ranks (×8)
Label Code		PC2700S–25330	PC2700S–25330
JEDEC SPD Revision		Rev. 0.0	Rev. 0.0
Byte#	**Description**	**HEX**	**HEX**
30	t_{RASmin} [ns]	2A	2A
31	Module Density per Rank	40	40
32	t_{AS}, t_{CS} [ns]	75	75
33	t_{AH}, t_{CH} [ns]	75	75
34	t_{DS} [ns]	45	45
35	t_{DH} [ns]	45	45
36 - 40	Not used	00	00
41	t_{RCmin} [ns]	3C	3C
42	t_{RFCmin} [ns]	48	48
43	t_{CKmax} [ns]	30	30
44	$t_{DQSQmax}$ [ns]	28	28
45	t_{QHSmax} [ns]	50	50
46	Not used	00	00
47	DIMM PCB Height	00	00
48 - 61	Not used	00	00
62	SPD Revision	00	00
63	Checksum of Byte 0-62	F8	F8
64	Manufacturer’s JEDEC ID Code (1)	7F	7F
65	Manufacturer’s JEDEC ID Code (2)	7F	7F
66	Manufacturer’s JEDEC ID Code (3)	7F	7F
67	Manufacturer’s JEDEC ID Code (4)	7F	7F
68	Manufacturer’s JEDEC ID Code (5)	7F	7F
69	Manufacturer’s JEDEC ID Code (6)	51	51
70	Manufacturer’s JEDEC ID Code (7)	00	00
71	Manufacturer’s JEDEC ID Code (8)	00	00
72	Module Manufacturer Location	xx	xx
73	Part Number, Char 1	36	36
74	Part Number, Char 2	34	34
75	Part Number, Char 3	44	44
76	Part Number, Char 4	36	36
77	Part Number, Char 5	34	34
78	Part Number, Char 6	30	30
79	Part Number, Char 7	32	32

Product Type		**HYS64D64020GBDL–6–C**	**HYS64D64020HBDL–6–C**
Organization		**512MB**	**512MB**
		×64	**×64**
		2 Ranks (×8)	**2 Ranks (×8)**
Label Code		**PC2700S–25330**	**PC2700S–25330**
JEDEC SPD Revision		**Rev. 0.0**	**Rev. 0.0**
Byte#	**Description**	**HEX**	**HEX**
80	Part Number, Char 8	30	30
81	Part Number, Char 9	47	48
82	Part Number, Char 10	42	42
83	Part Number, Char 11	44	44
84	Part Number, Char 12	4C	4C
85	Part Number, Char 13	36	36
86	Part Number, Char 14	43	43
87	Part Number, Char 15	20	20
88	Part Number, Char 16	20	20
89	Part Number, Char 17	20	20
90	Part Number, Char 18	20	20
91	Module Revision Code	1x	1x
92	Test Program Revision Code	xx	xx
93	Module Manufacturing Date Year	xx	xx
94	Module Manufacturing Date Week	xx	xx
95 - 98	Module Serial Number	xx	xx
99 - 127	Not used	00	00

5 Package Outlines

This chapter contains the package outlines of the products.

FIGURE 2
Package Outline SO-DIMM L-DIM-200-22

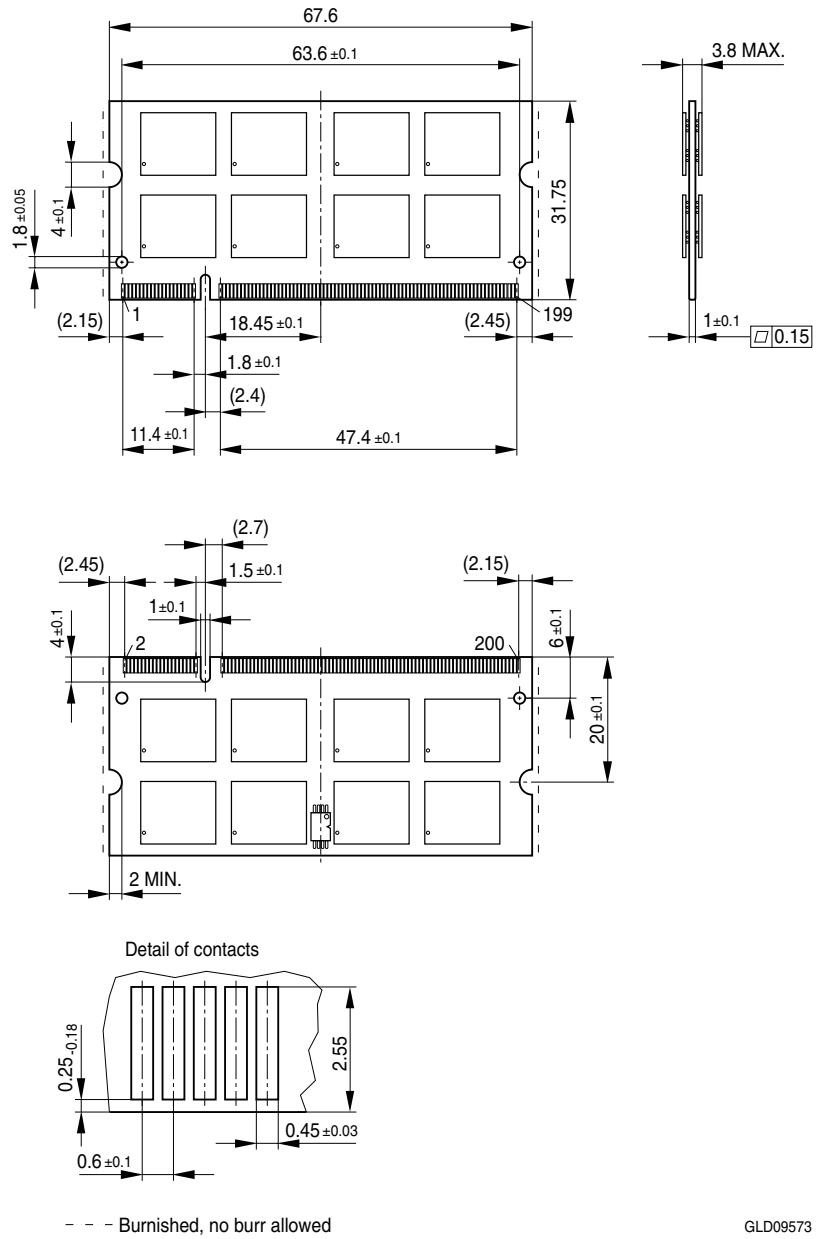

Table of Contents

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